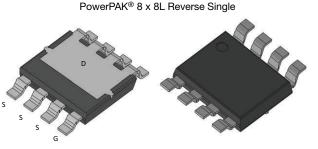
SQJQ184ER

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Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET



Top View

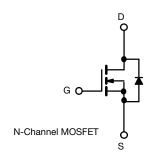
Bottom View

PRODUCT SUMMARY			
V _{DS} (V)	80		
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0014		
I _D (A)	430		
Configuration	Single		
Package	PowerPAK 8 x 8L Reverse		

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATINGS	$(T_C = 25 \circ C, unles)$	s otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	80	 	
Gate-source voltage		V _{GS}	± 20	- V	
Continuous drain current	T _C = 25 °C		430		
	T _C = 125 °C	- I _D	250		
Continuous source current (diode conduction)		۱ _S	450	А	
Pulsed drain current ^a		I _{DM}	1200		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	65		
Single pulse avalanche energy		E _{AS}	211	mJ	
Maximum power dissipation	T _C = 25 °C	D	600	w	
	T _C = 125 °C	P _D	200	vv	
Operating junction and storage temperature range Soldering recommendations (peak temperature) ^c		T _J , T _{stg}	-55 to +175	°C	
			260	-0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	40	°C/W
Junction-to-case (drain)		R _{thJC}	0.25	0/10

Notes

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

1

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

MAX.

UNIT

MIN.

TYP.

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SPECIFICATIONS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS			
Static					
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$			
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$			

Static								
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	80	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		2	3	3.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	500		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	Α	
Drain-source on-state resistance ^a		V _{GS} = 10 V	I _D = 20 A	-	0.0012	0.0014	Ω	
	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.00281		
		$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.0037		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	82	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz	-	11 435	16 009	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	1896	2655		
Reverse transfer capacitance	C _{rss}			-	92	129		
Total gate charge ^c	Qg		V _{GS} = 10 V V _{DS} = 40 V, I _D = 10 A	-	183	240	nC	
Gate-source charge c	Q _{gs}	$V_{GS} = 10 V$		-	47	-		
Gate-drain charge ^c	Q _{gd}			-	85	-		
Gate resistance	Rg	f = 1 MHz		0.7	1.3	2	Ω	
Turn-on delay time ^c	t _{d(on)}			-	21	28		
Rise time ^c	t _r	V _{DD} =	$V_{DD} = 40 \text{ V}, \text{ R}_{\text{I}} = 0.8 \Omega$		80	105	ns	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	65	85		
Fall time ^c	t _f			-	20	28		
Source-Drain Diode Ratings and Cha	aracteristics ^b							
Pulsed current ^a	I _{SM}			-	-	1100	Α	
Forward voltage	V _{SD}	$I_{\rm F} = 40 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.7	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

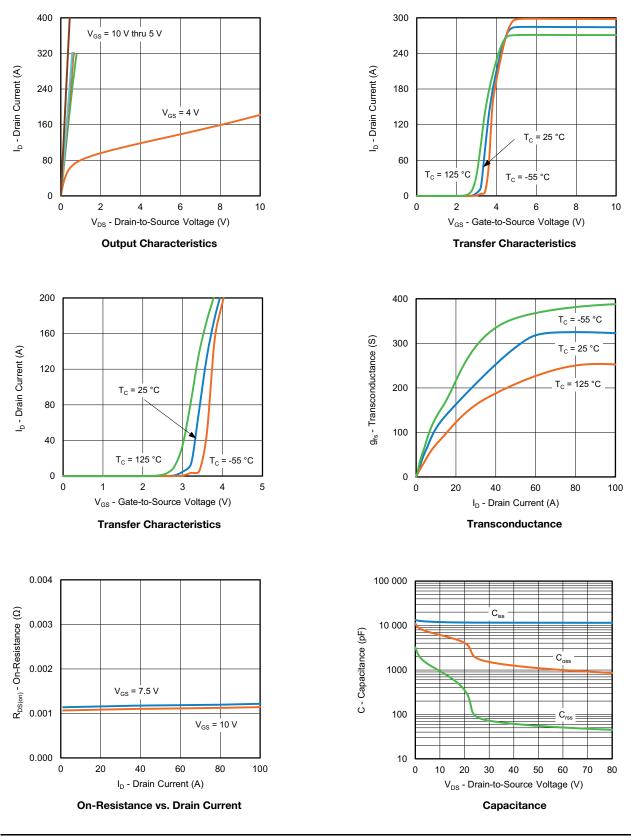
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



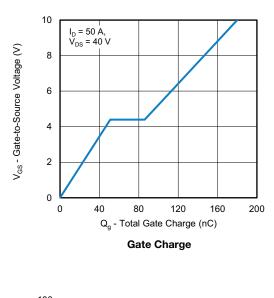
S22-0114-Rev. A, 14-Feb-2022

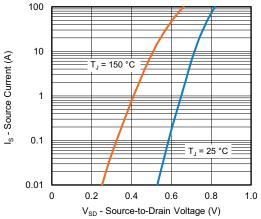
3 s. contact: automostech Document Number: 71298

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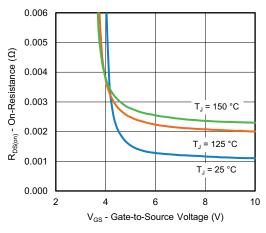


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

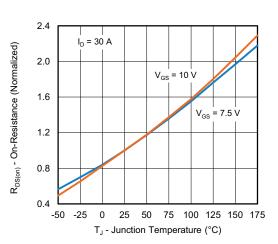




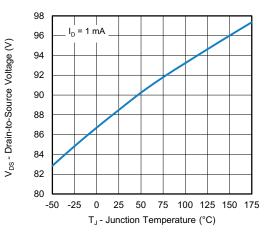
Source Drain Diode Forward Voltage



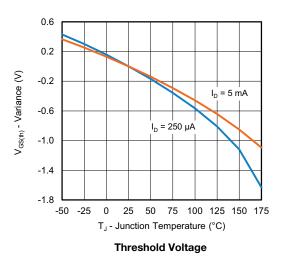
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature



S22-0114-Rev. A, 14-Feb-2022

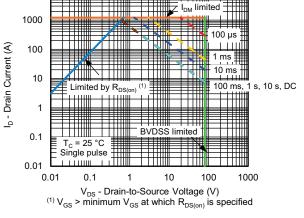
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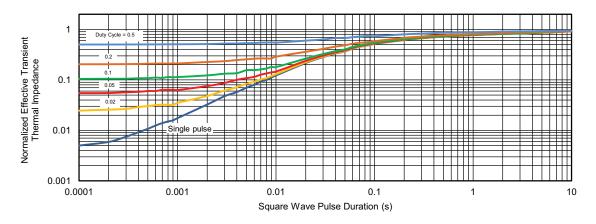


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

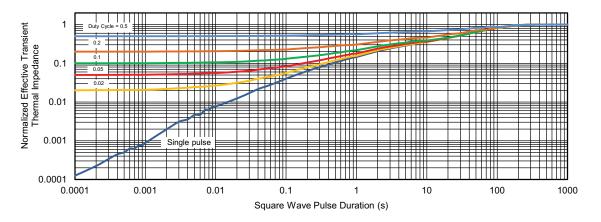
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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